

Title (en)
METHOD FOR PRODUCTION OF A SEMICONDUCTOR COMPONENT AND A SEMICONDUCTOR COMPONENT PRODUCED BY SAID METHOD

Title (de)
VERFAHREN ZUR HERSTELLUNG EINES HALBLEITERBAUELEMENTS SOWIE EIN NACH DEM VERFAHREN HERGESTELLTES HALBLEITERBAUELEMENT

Title (fr)
PROCEDE POUR PRODUIRE UN COMPOSANT A SEMICONDUCTEURS ET COMPOSANT A SEMICONDUCTEURS AINSI PRODUIT

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Application
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Abstract (en)
[origin: WO0202458A1] The invention relates to a method for the production of a semiconductor component (100; ; 2200), in particular, a multi-layered semiconductor component, preferably a micromechanical component, such as, in particular, a pressure sensor, comprising a semiconductor substrate (101), in particular, made from silicon and a semiconductor component produced by said method. The invention particularly relates to the reduction of the production costs of such a semiconductor component by developing the method such that, in a first step, a first porous layer (104; 1001; 1301) is formed in the semiconductor component and, in a second step, a cavity or a cavern (201; 1101; 1201; 1401; 2101; 2201) is formed under, or from, the first porous layer (104; 1001; 1301) in the semiconductor component. Said cavity or cavern can be provided with an external entry opening.

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